

# ZXMP3A17DN8

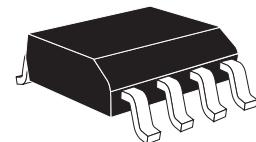
## DUAL P-CHANNEL 30V ENHANCEMENT MODE MOSFET

### SUMMARY

$V_{(BR)DSS} = -30V$ ;  $R_{DS(ON)} = 0.070\Omega$ ;  $I_D = -4.4A$

### DESCRIPTION

This new generation of TRENCH MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



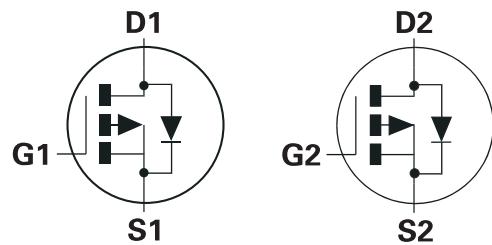
SO8

### FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

### APPLICATIONS

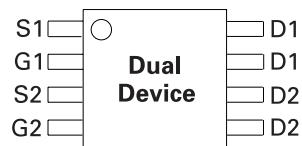
- Motor Drive
- LCD backlighting



### ORDERING INFORMATION

DEVICE	REEL	TAPE WIDTH	QUANTITY PER REEL
ZXMP3A17DN8TA	7"	12mm	500 units
ZXMP3A17DN8TC	13"	12mm	2500 units

### PINOUT



Top view

# ZXMP3A17DN8

## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DSS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current@ $V_{GS}=10V$ ; $T_A=25^\circ C$ (b)(d) @ $V_{GS}=10V$ ; $T_A=70^\circ C$ (b)(d) @ $V_{GS}=10V$ ; $T_A=25^\circ C$ (a)(d)	$I_D$	-4.4 -3.6 -3.4	A A A
Pulsed Drain Current (c)	$I_{DM}$	-16.2	A
Continuous Source Current (Body Diode)(b)	$I_S$	-2.5	A
Pulsed Source Current (Body Diode)(c)	$I_{SM}$	-16.2	A
Power Dissipation at $TA=25^\circ C$ (a)(d) Linear Derating Factor	$P_D$	1.25 10	W mW/ $^\circ C$
Power Dissipation at $TA=25^\circ C$ (a)(e) Linear Derating Factor	$P_D$	1.8 14	W mW/ $^\circ C$
Power Dissipation at $TA=25^\circ C$ (b)(d) Linear Derating Factor	$P_D$	2.1 17	W mW/ $^\circ C$
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ C$

## THERMAL RESISTANCE

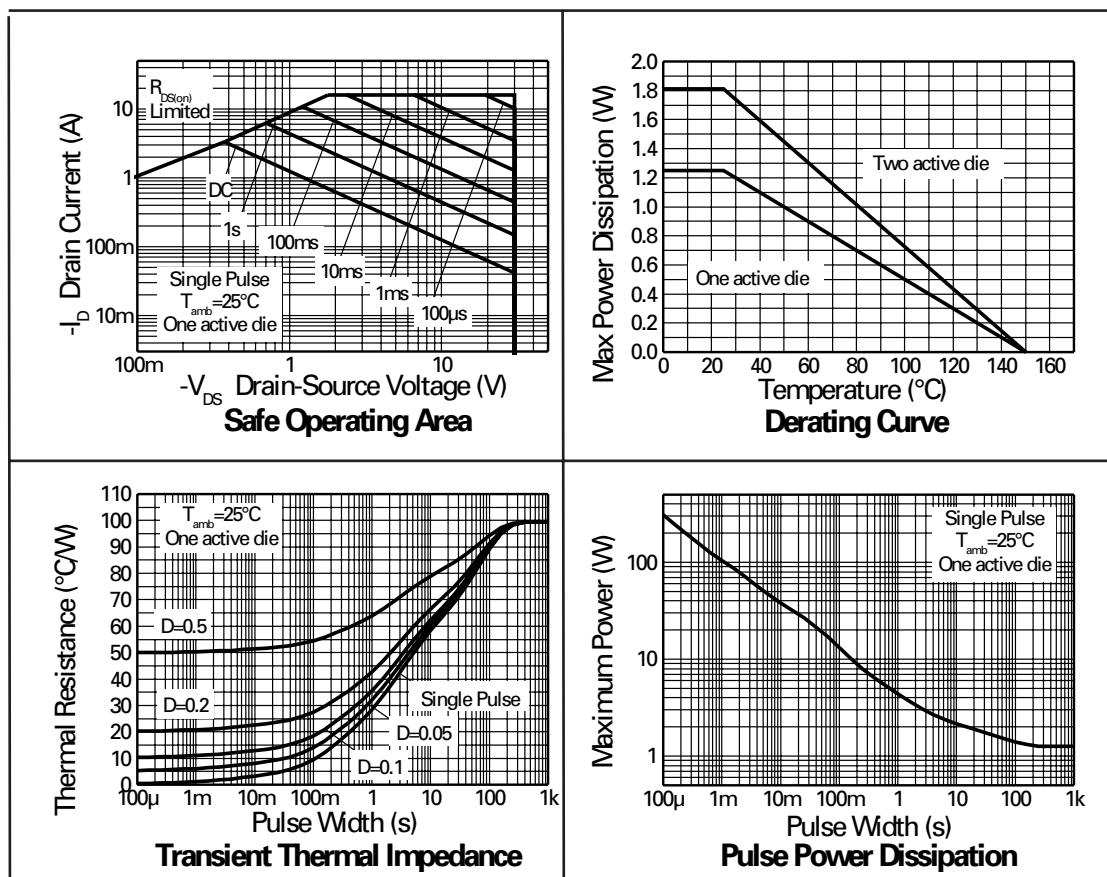
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(d)	$R_{\theta JA}$	100	$^\circ C/W$
Junction to Ambient (b)(e)	$R_{\theta JA}$	70	$^\circ C/W$
Junction to Ambient (b)(d)	$R_{\theta JA}$	60	$^\circ C/W$

### Notes

- (a) For a dual device surface mounted on 25mm x 25mm FR4 PCB with coverage of single sided 1oz copper in still air conditions.
- (b) For a dual device surface mounted on FR4 PCB measured at  $t \leq 10$  sec.
- (c) Repetitive rating 25mm x 25mm FR4 PCB,  $D=0.05$  pulse width= $10\mu s$  - pulse width limited by maximum junction temperature.
- (d) For a dual device with one active die.
- (e) For dual device with 2 active die running at equal power.

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## CHARACTERISTICS



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**ELECTRICAL CHARACTERISTICS** (at  $T_{amb} = 25^\circ C$  unless otherwise stated).

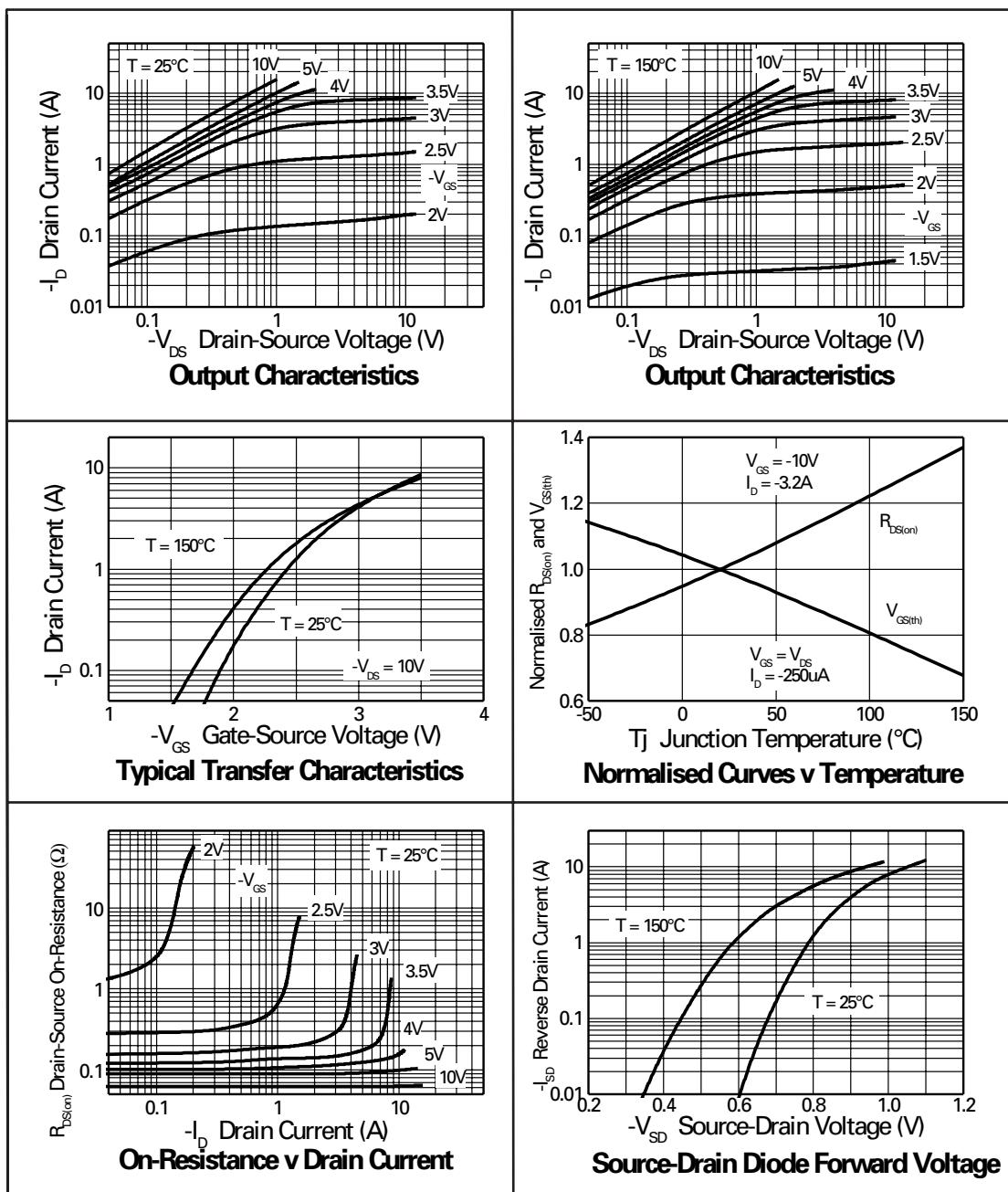
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-30			V	$I_D=-250\mu A, V_{GS}=0V$
Zero Gate Voltage Drain Current	$I_{DSS}$			-1.0	$\mu A$	$V_{DS}=-30V, V_{GS}=0V$
Gate-Body Leakage	$I_{GSS}$			100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.0			V	$I_D=-250\mu A, V_{DS}= V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.070 0.110	$\Omega$	$V_{GS}=-10V, I_D=-3.2A$ $V_{GS}=-4.5V, I_D=-2.5A$
Forward Transconductance (1)(3)	$g_{fs}$		6.4		S	$V_{DS}=-15V, I_D=-3.2A$
<b>DYNAMIC (3)</b>						
Input Capacitance	$C_{iss}$		630		pF	$V_{DS}=-15V, V_{GS}=0V,$ $f=1MHz$
Output Capacitance	$C_{oss}$		113		pF	
Reverse Transfer Capacitance	$C_{rss}$		78		pF	
<b>SWITCHING(2) (3)</b>						
Turn-On Delay Time	$t_{d(on)}$		1.74		ns	$V_{DD}=-15V, I_D=-1A$ $R_G=6.0\Omega, V_{GS}=-10V$
Rise Time	$t_r$		2.87		ns	
Turn-Off Delay Time	$t_{d(off)}$		29.2		ns	
Fall Time	$t_f$		8.72		ns	
Gate Charge	$Q_g$		8.28		nC	$V_{DS}=-15V, V_{GS}=-5V,$ $I_D=-3.2A$
Total Gate Charge	$Q_g$		15.8		nC	$V_{DS}=-15V, V_{GS}=-10V,$ $I_D=-3.2A$
Gate-Source Charge	$Q_{gs}$		1.84		nC	
Gate-Drain Charge	$Q_{gd}$		2.80		nC	
<b>SOURCE-DRAIN DIODE</b>						
Diode Forward Voltage (1)	$V_{SD}$		-0.85	-1.2	V	$T_J=25^\circ C, I_S=-2.5A,$ $V_{GS}=0V$
Reverse Recovery Time (3)	$t_{rr}$		19.5		ns	$T_J=25^\circ C, I_F=-1.7A,$ $di/dt= 100A/\mu s$
Reverse Recovery Charge (3)	$Q_{rr}$		16.3		nC	

## NOTES

- (1) Measured under pulsed conditions. Width  $\leq 300\mu s$ . Duty cycle  $\leq 2\%$ .
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.

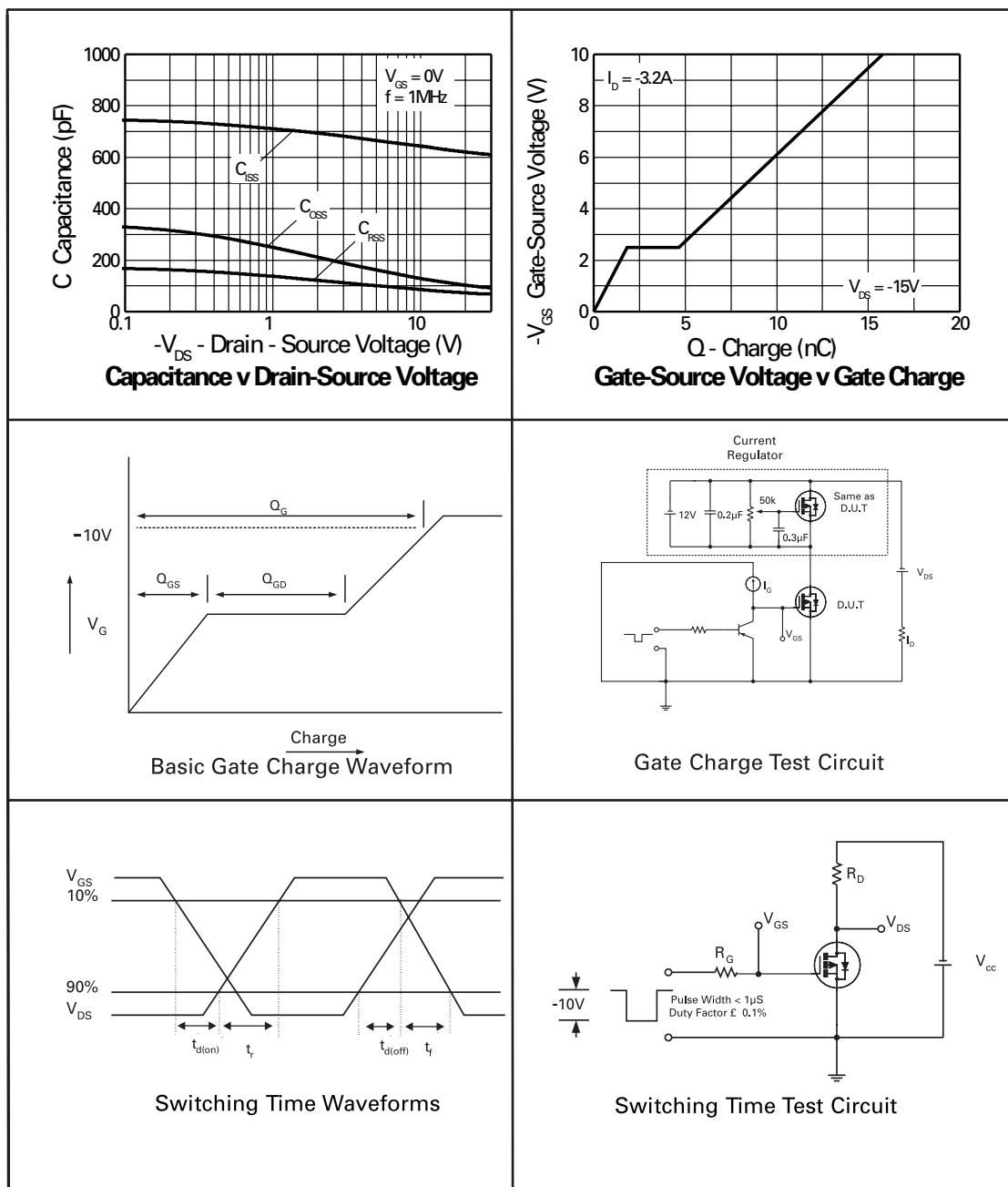
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## TYPICAL CHARACTERISTICS



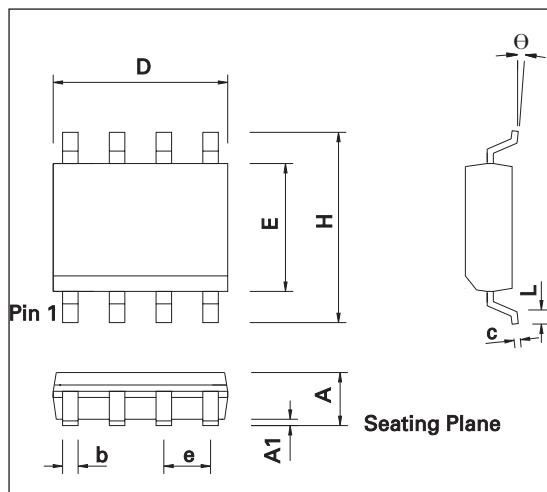
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## TYPICAL CHARACTERISTICS



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## PACKAGE OUTLINE



CONTROLLING DIMENSIONS ARE IN INCHES  
APPROX IN MILLIMETRES

## PACKAGE DIMENSIONS

DIM	INCHES		MILLIMETRES	
	MIN	MAX	MIN	MAX
A	0.053	0.069	1.35	1.75
A1	0.004	0.010	0.10	0.25
D	0.189	0.197	4.80	5.00
H	0.228	0.244	5.80	6.20
E	0.150	0.157	3.80	4.00
L	0.016	0.050	0.40	1.27
e	0.050 BSC		1.27 BSC	
b	0.013	0.020	0.33	0.51
c	0.008	0.010	0.19	0.25
Θ	0°	8°	0°	8°
h	0.010	0.020	0.25	0.50

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